

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK4059TV

For ECM

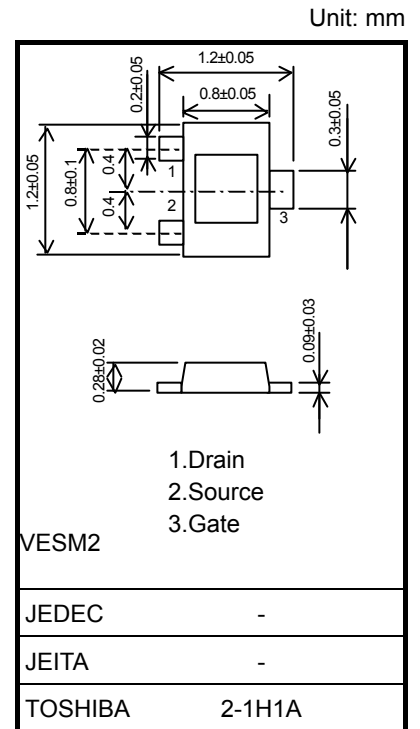
- Application for Ultra-compact ECM

Absolute Maximum Ratings (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Gate-Drain voltage	V _{GD0}	-20	V
Gate Current	I _G	10	mA
Drain power dissipation (Ta = 25°C)	P _D	100	mW
Junction Temperature	T _j	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

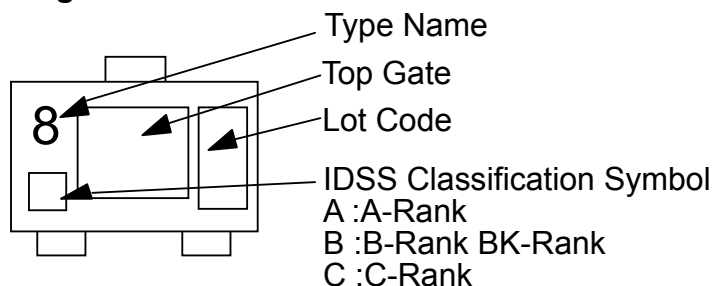


Weight: 0.8mg (typ.)

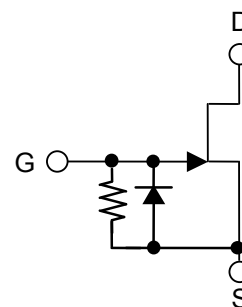
IDSS CLASSIFICATION

A-Rank	140~240μA
B-Rank	210~350μA
BK-Rank	210~400μA
C-Rank	320~500μA

Marking



Equivalent Circuit



Precaution

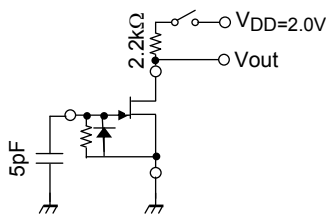
There is a metal plate on the top of package, which has the same electrical potential as the Gate terminal. Don't use it as a terminal.

Electrical Characteristics (Ta=25°C)

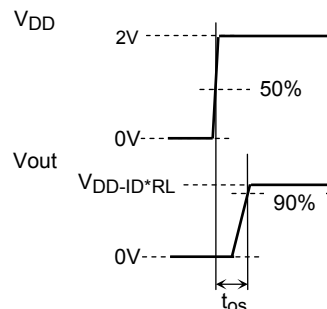
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit	
Drain Current	I _{DSS}	V _{DS} = 2 V, V _{GS} = 0	A	140	—	240	μA
			B	210	—	350	
			BK	210	—	400	
			C	320	—	500	
Drain Current	I _D	V _{DD} = 2 V, R _L = 2.2kΩ, C _g = 5pF	A	125	—	260	μA
			B	190	—	370	
			BK	190	—	420	
			C	290	—	500	
Gate-Source Cut-off Voltage	V _{GS(OFF)}	V _{DS} = 2 V, I _D = 1μA	-0.1	—	-1.0	V	
Forward transfer admittance	Y _{fs}	V _{DS} = 2 V, V _{GS} = 0V	1.35	1.85	—	mS	
Gate-Drain Voltage	V _{(BR)GDO}	I _G = -10μA	-20	—	—	V	
Input capacitance	C _{iss}	V _{DS} = 2 V, V _{GS} = 0, f = 1 MHz	—	4.0	—	pF	
Voltage Gain	G _v	V _{DD} = 2V, R _L = 2.2kΩ, C _g = 5pF, f = 1kHz, v _{in} = 100mV	A	-1.2	+0.9	—	dB
			B	-0.2	+1.4	—	
			BK	-0.2	+1.7	—	
			C	+0.5	+1.8	—	
Delta Voltage Gain	DG _{v(f)}	V _{DD} = 2V, R _L = 2.2kΩ, C _g = 5pF, f = 1kHz~100Hz, v _{in} = 100mV	—	0	-1	dB	
Delta Voltage Gain	DG _{v(V)}	V _{DD} = 2V~1.5V, R _L = 2.2kΩ, C _g = 5pF, f = 1kHz, v _{in} = 100mV	A	—	-0.6	-1.1	dB
			B	—	-0.8	-1.7	
			BK	—	-1.1	-2.0	
			C	—	-1.4	-3.2	
Noise Voltage	V _N	V _{DD} = 2V, R _L = 1kΩ, C _g = 10pF, G _v = 80dB, A-Curve Filter	A	—	33	75	mV
			B	—	38	80	
			BK	—	40	85	
			C	—	42	90	
Total Harmonic Distortion	THD	V _{DD} = 2V, R _L = 2.2kΩ, C _g = 5pF, f = 1kHz, v _{in} = 50mV	A	—	1.3	—	%
			B	—	0.6	—	
			BK	—	0.5	—	
			C	—	0.1	—	
Time Output Stability	t _{os}	V _{DD} = 2V, R _L = 2.2kΩ, C _g = 5pF	—	100	200	ms	

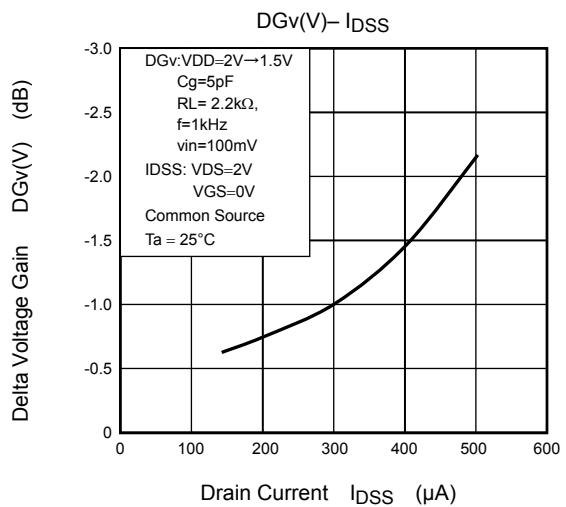
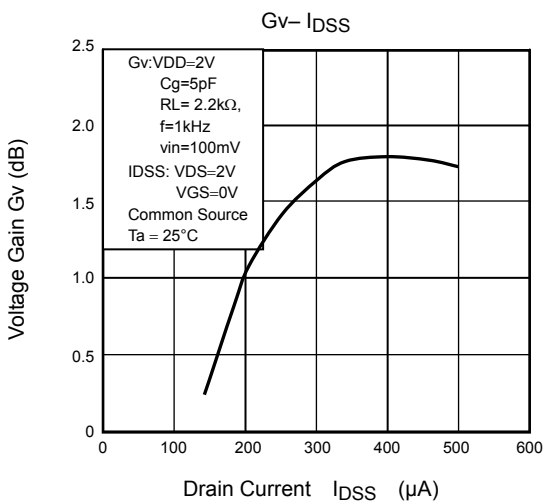
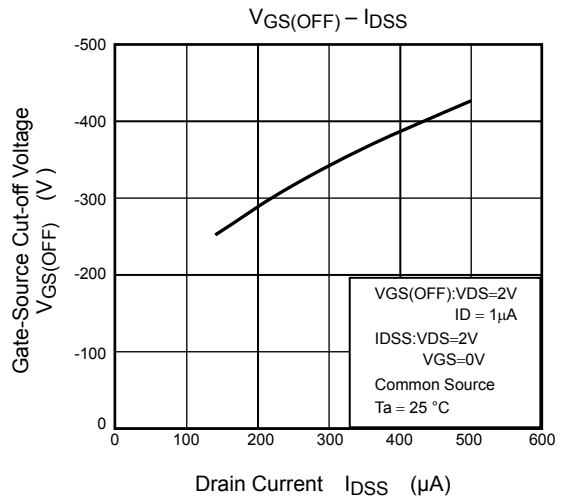
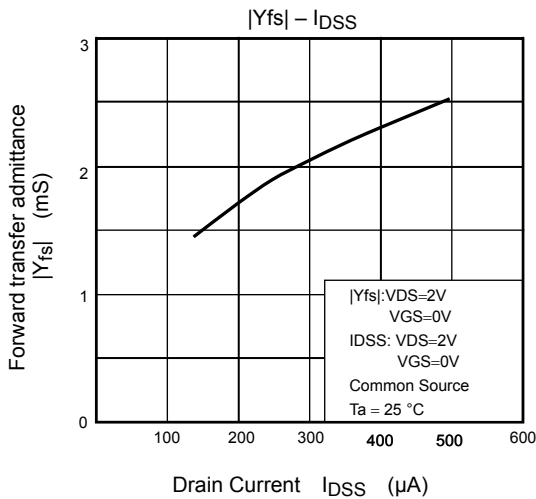
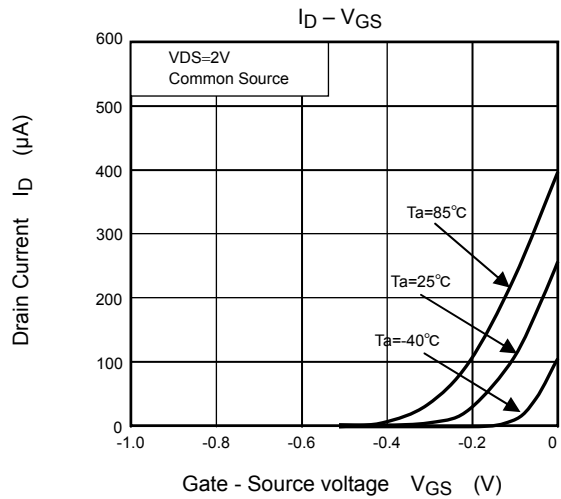
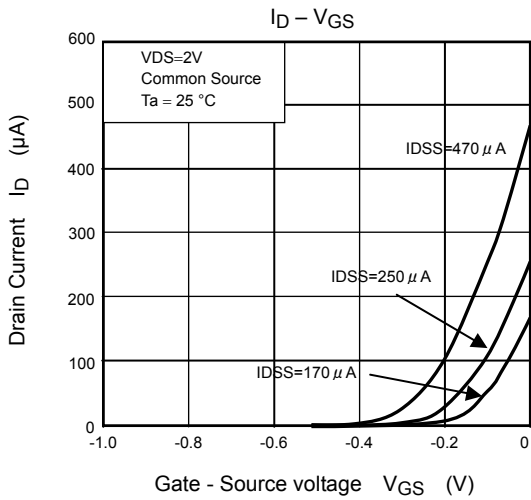
Time Output Stability Test Method

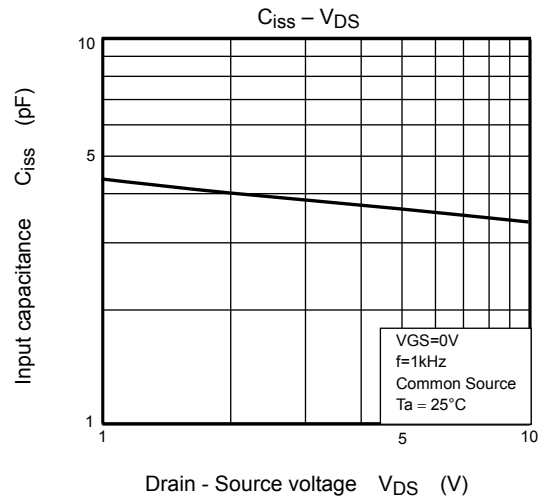
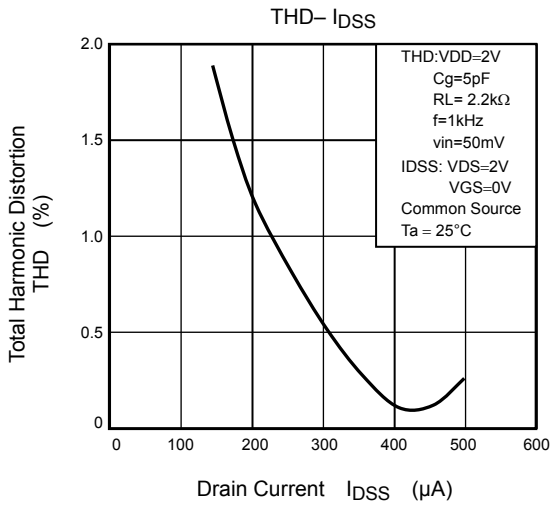
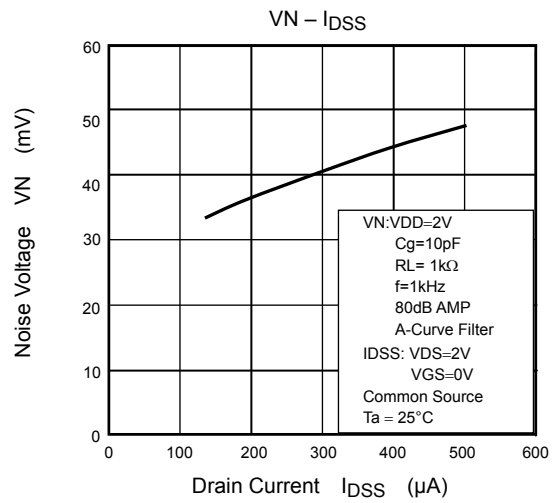
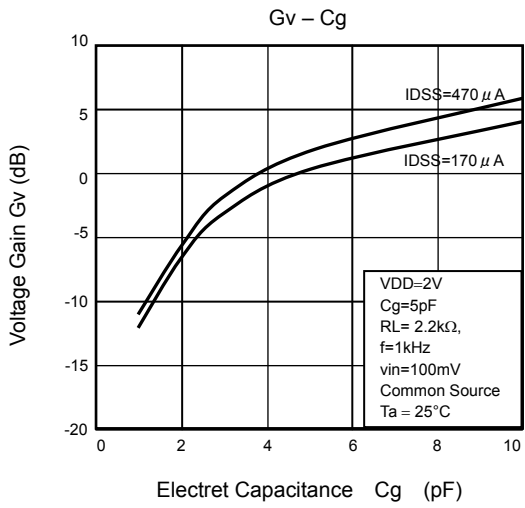
a) TEST CIRCUIT



b) TEST SIGNAL







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20070701-EN GENERAL

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